MC74LVX132

Quad 2-Input NAND Schmitt Trigger

The MC74LVX132 is an advanced high speed CMOS Schmitt NAND trigger fabricated with silicon gate CMOS technology.

Pin configuration and function are the same as the MC74LVX00, but the inputs have hysteresis.

The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 5.8 \text{ ns}$ (Typ) at $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Low Noise: $V_{OLP} = 0.5 V (Max)$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V; Machine Model > 200 V
- These Devices are Pb-Free and are RoHS Compliant



Figure 1. Logic Diagram

FUNCTION TABLE

A Input	B Input	Y Output
L	L	Н
L	н	Н
н	L	н
н	н	L



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D SUFFIX CASE 751A

TSSOP-14 DT SUFFIX CASE 948G





MARKING DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	F	Parameter	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage		–0.5 to V _{CC} +0.5	V
Ι _{ΙΚ}	DC Input Diode Current	V _I < GND	-20	mA
I _{OK}	DC Output Diode Current	V _O < GND	±20	mA
I _{OUT}	DC Output Sink Current		±25	mA
I _{CC}	DC Supply Current per Supply Pin		±50	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for	10 Seconds	260	°C
TJ	Junction Temperature under Bias		+ 150	°C
θ_{JA}	Thermal Resistance	SOIC TSSOP	250	°C/W
P _D	Power Dissipation in Still Air at 85°C	SOIC TSSOP	250	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% – 35%	UL 94-V0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 2000 > 200 N/A	V
I _{Latchup}	Latchup Performance	Above V_{CC} and Below GND at 85°C (Note 4)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Tested to EIA/JESD22-A114-A.

Tested to EIA/JESD22–A115–A.
Tested to JESD22–C101–A.

4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Supply Voltage	2.0	3.6	V
VI	Input Voltage (Note 5)	0	5.5	V
Vo	Output Voltage (HIGH or LOW State)	0	5.5	V
T _A	Operating Free–Air Temperature	- 40	+ 125	°C
$\Delta t / \Delta V$	Input Transition Rise or Fall Rate $V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

5. Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

			v _{cc}	٦	T _A = 25°C		T _A = ≤	≦ 85°C	TA = ≤	125°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{T+}	Positive Threshold Voltage (Figure 4)		2.0 3.0 3.6	1.15 1.50 1.70	1.31 1.82 2.12	1.60 2.25 2.60	1.15 1.50 1.70	1.60 2.25 2.60	1.15 1.50 1.70	1.60 2.25 2.60	V
V _{T-}	Negative Threshold Voltage (Figure 4)		2.0 3.0 3.6	0.30 0.75 1.00	0.64 1.13 1.46	0.9 1.45 1.90	0.30 0.75 1.00	0.90 1.45 1.90	0.30 0.75 1.00	0.90 1.45 1.90	V
V _H	Hysteresis Voltage (Figure 4)		2.0 3.0 3.6	0.30 0.30 0.35	0.70 0.76 0.69	1.30 1.50 1.60	0.30 0.30 0.35	1.30 1.50 1.60	0.30 0.30 0.35	1.30 1.50 1.60	V
V _{OH}	Minimum High–Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -50 \ \mu A$ $I_{OH} = -50 \ \mu A$ $I_{OH} = -4 \ m A$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		1.9 2.9 2.34		V
V _{OL}	Maximum Low–Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 50 \ \mu A$ $I_{OL} = 50 \ \mu A$ $I_{OL} = 4 \ m A$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44		0.1 0.1 0.52	V
l _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	3.6			±0.1		±1.0		±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	3.6			2.0		20		20	μΑ

DC ELECTRICAL CHARACTERISTICS

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0ns)

					T _A = 25°C	2	T _A = ≤	≦ 85°C	T _A = ≤	125°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay,	V _{CC} = 2.7V	$C_L = 15pF$ $C_L = 50pF$		7.0 10.0	11.0 16.0	1.0 1.0	13.0 18.7	1.0 1.0	15.0 20.0	ns
	A or B to Y	$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$		5.8 8.3	10.6 15.4	1.0 1.0	12.5 17.5	1.0 1.0	14.5 19.5	
t _{OSHL} ,	Output to Output Skew	V _{CC} = 2.7V	$C_L = 50 pF$			1.5		1.5		1.5	ns
toslh	(Note 6)	$V_{CC}=3.3\pm0.3V$	$C_L = 50 pF$			1.5		1.5		1.5	
C _{in}	Maximum Input Capacitance				4	10		10		10	pF
					Ту	pical @	25°C, V	_{CC} = 5.0	v		
C _{PD}	Power Dissipation Capacitance (Note 6)		11				pF				

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/4$ (per gate). C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, C_L = 50pF, V_{CC} = 5.0 V)

		T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.5	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.5	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V



Figure 2. Switching Waveforms



*Includes all probe and jig capacitance

Figure 3. Test Circuit



Figure 4. Typical Input Threshold, V_{T+} , V_{T-} versus Power Supply Voltage

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(a) A Schmitt-Trigger Squares Up Inputs With Slow Rise and Fall Times

(b) A Schmitt-Trigger Offers Maximum Noise Immunity





Figure 6. Input Equivalent Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LVX132DR2G	SOIC-14 NB (Pb-Free)	2500 Tape & Reel
MC74LVX132DTG	TSSOP-14 (Pb-Free)	96 Units / Rail
MC74LVX132DTR2G	TSSOP-14 (Pb-Free)	2500 Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G **ISSUE B**



NOTES: 1. DIMENSIONING AND TOLERANCING PER

DIRENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MILLIMETER.
DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
TERLEAD FLASH OR PROTRUSION AT MAXIMUM MATERIAL CONDITION.

MIAI ERIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE --W-.

DETERMINED AT	DATON PLANE -W	

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252 BSC	
М	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT*





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PACKAGE DIMENSIONS



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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